

Data Sheet

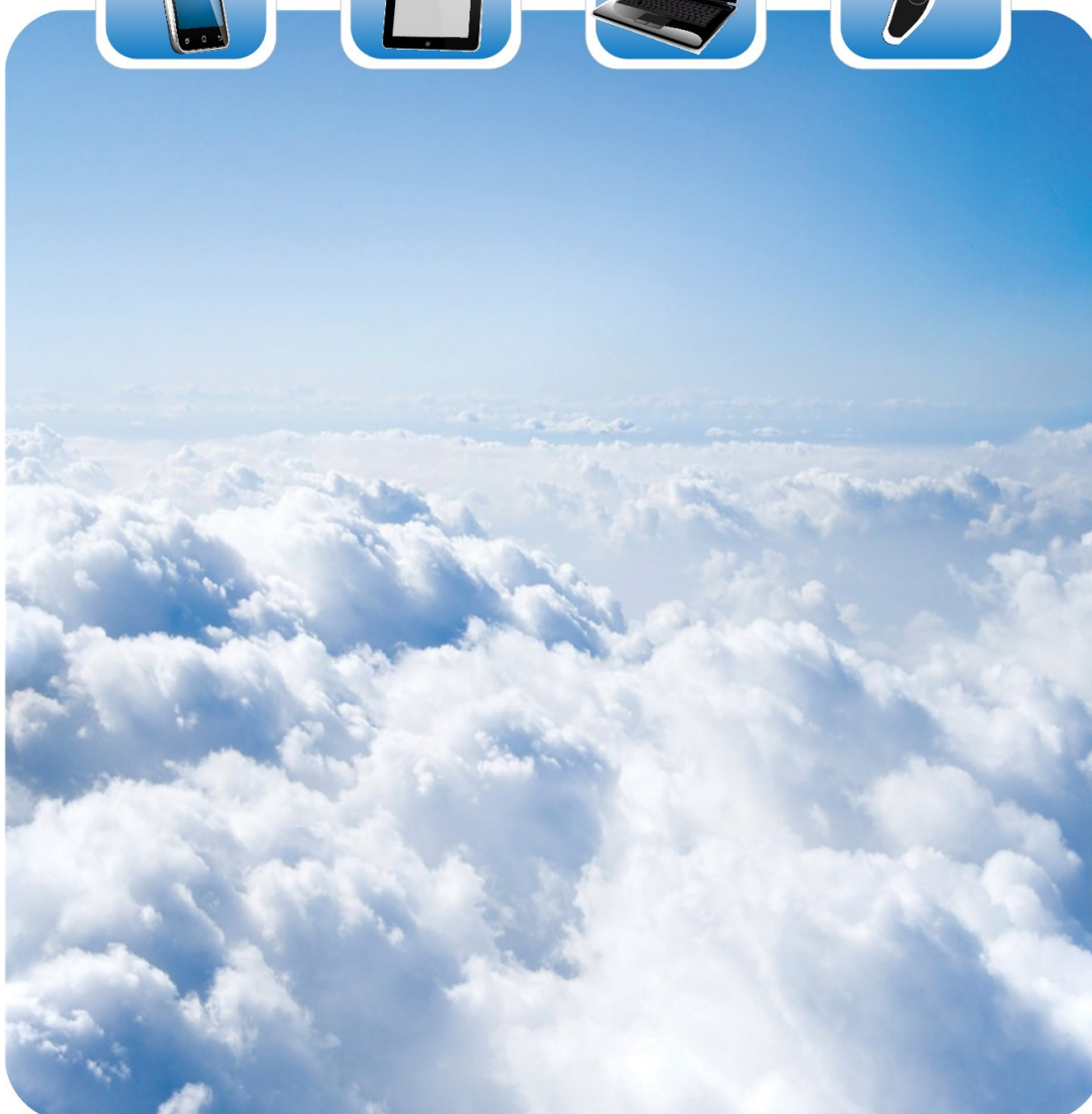
V 1.3 / Oct. 2017

MSM261D4030H1AP

PDM digital output MEMS microphone with Multi-modes



苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



购买原装正品请认准-德方电子
免费服务热线: 400-655-8700
深圳总部电话: 0755-28187877
网址: www.denovocn.com

MSM261D4030H1AP

PDM digital output MEMS microphone



苏州敏芯微电子技术股份有限公司

MEMSensing Microsystems (Suzhou, China) Co., Ltd.



GENERAL DESCRIPTION

MSM261D4030H1AP is an omnidirectional, Top-ported, PDM digital output MEMS microphone. It has high performance and reliability.

MSM261D4030H1AP is available in a thin 4 mm × 3 mm × 1 mm proprietary OCLGA package. It is SMT compatible with no sensitivity degradation.

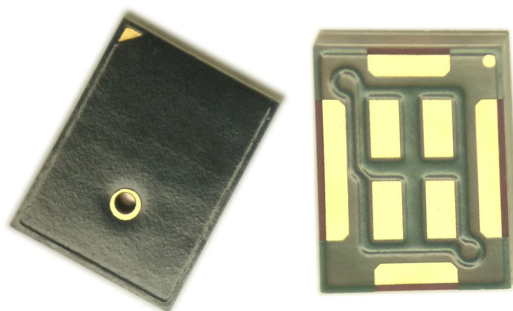
APPLICATIONS

- ✧ Mobile Phone
- ✧ Laptop
- ✧ Tablet computer
- ✧ Bluetooth headset
- ✧ Earphone
- ✧ Wearable intelligent equipment

FEATURES

- ✧ High SNR
- ✧ Fourth-order Σ - Δ modulator
- ✧ Digital PDM output
- ✧ Compatible with Sn/Pb and Pb-free solder processes
- ✧ RoHS/Halogen free compliant
- ✧ Multiple performance modes (Sleep, Low-Power, Standard Performance)
- ✧ Sensitivity Matching within +/-1dB

PRODUCT VIEW



MSM261D4030H1AP

PDM digital output MEMS microphone



苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



ABSOLUTE MAXIMUM RATINGS

Parameter	Maximum value	Unit
Supply Voltage	-0.3 to 4.0	V
Sound Pressure Level	140	dB SPL
Temperature Range	-40 to 100	°C
Electrostatic discharge protection	2 (HBM)	kV

ACOUSTIC & ELECTRICAL SPECIFICATIONS

TEST CONDITIONS: 23 ±2°C, 55±20% R.H., VDD=1.8 V, f_{CLOCK}=2.4 MHz, SELECT pin grounded, no load, unless otherwise indicate

General Microphone Specifications

Parameter		Symbol	Conditions	Min	Typ	Max	Units
Supply Voltage		V _{DD}		1.6	-	3.6	V
Clock Frequency Range	Sleep Mode			0		50	KHz
	Low-Power Mode			150		900	KHz
	Standard Performance Mode			1.1		4.0	MHz
Sleep Current		I _{SLEEP}	f _{CLOCK} ≤ 50 kHz	-	1		μA
DC Output			Fullscale = ±100	-	4	-	% FS
Directivity				Omnidirectional			
Polarity			Increasing sound	increasing density of 1's			
Data Format				½ Cycle PDM			
Short Circuit Current		I _{SC}	Grounded DATA pin	1	-	10	mA
Output Load		C _{LOAD}		-	-	200	pF
Fall-asleep Time			f _{CLOCK} ≤ 50 kHz	-	-	30	μs
Wake-up Time			f _{CLOCK} ≥ 151 kHz	-	-	200	μs
Power-up Time			V _{DD} ≥ V(min)	-	-	50	ms
Mode-Change Time				-	-	10	ms

MSM261D4030H1AP

PDM digital output MEMS microphone



苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



Standard Performance Mode

TEST CONDITIONS: $f_{\text{CLOCK}} = 2.4 \text{ MHz}$, $V_{\text{DD}} = 1.8 \text{ V}$, unless otherwise indicated

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Current	I_{DD}	$f_{\text{CLOCK}} = 2.4 \text{ MHz}$	-	670	-	μA
Sensitivity	S	94 dB SPL @ 1 kHz	-27	-26	-25	dBFS
Signal to Noise Ratio	SNR	20 kHz bandwidth, A-weighted $f_{\text{CLOCK}} = 2.4 \text{ MHz}$	-	64	-	dB(A)
Total Harmonic Distortion	THD	94 dB SPL @ 1 kHz, S = Typ	-	0.2	-	%
Acoustic Overload Point	AOP	10% THD @ 1 kHz, S = Typ	-	120	-	dB SPL
Power Supply Rejection Ratio	PSRR	200 mVpp sine wave @ 1 kHz	-	50	-	dBV/FS
Power Supply Rejection	PSR+N	100 mVpp square wave @ 217 Hz, A-weighted	-	-80	-	dBFS(A)

MSM261D4030H1AP

PDM digital output MEMS microphone


 苏州敏芯微电子技术股份有限公司
 MEMSensing Microsystems (Suzhou, China) Co., Ltd.
**Low-Power Mode**TEST CONDITIONS: $f_{\text{CLOCK}} = 768 \text{ kHz}$, $V_{\text{DD}} = 1.8 \text{ V}$, unless otherwise indicated

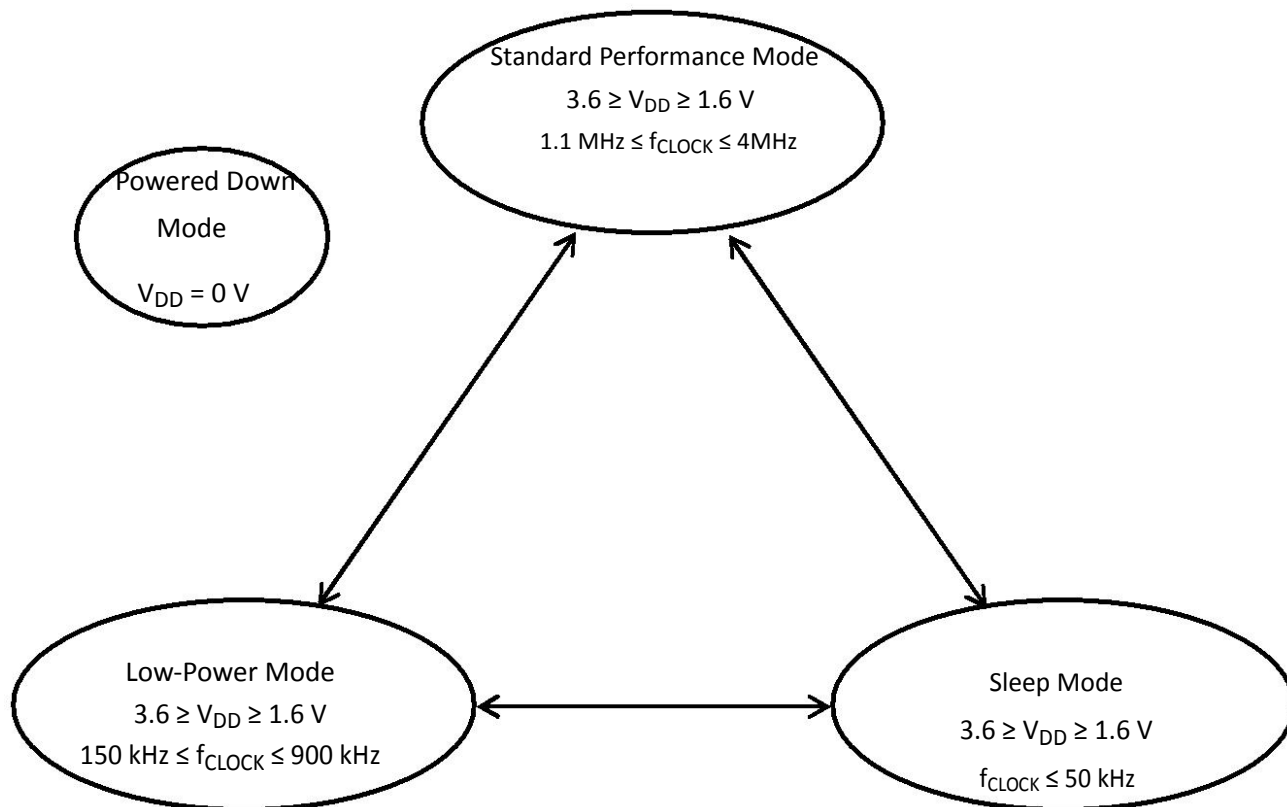
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Current	I_{DD}	$f_{\text{CLOCK}} = 768 \text{ KHz}$	-	290	-	μA
Sensitivity	S	94 dB SPL @ 1 kHz	-26	-25	-24	dBFS
Signal to Noise Ratio	SNR	94 dB SPL @ 1 kHz, A-weighted(20Hz-8KHz)	-	62	-	dB(A)
Total Harmonic Distortion	THD	94 dB SPL @ 1 kHz, S = Typ	-	0.2	-	%
Acoustic Overload Point	AOP	10% THD @ 1 kHz, S = Typ	-	120	-	dB SPL
Power Supply Rejection Ratio	PSRR	200 mVpp sinewave @ 1 kHz	-	50	-	dBV/FS
Power Supply Rejection	PSR+N	100 mVpp square wave @ 217 Hz, A-weighted(20Hz-8KHz)	-	-80	-	dBFS(A)

Microphone Interface Specifications

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Logic Input High	V_{IH}		$0.7 \times V_{\text{DD}}$	-	3.6	V
Logic Input Low	V_{IL}		-0.3	-	$0.3 \times V_{\text{DD}}$	V
Logic Output High	V_{OH}	$I_{\text{OUT}} = 2 \text{ mA}$	$V_{\text{DD}} - 0.45$	-	-	V
Logic Output Low	V_{OL}	$I_{\text{OUT}} = 2 \text{ mA}$	-	-	0.45	V
Clock Duty Cycle		-	40	-	60	%

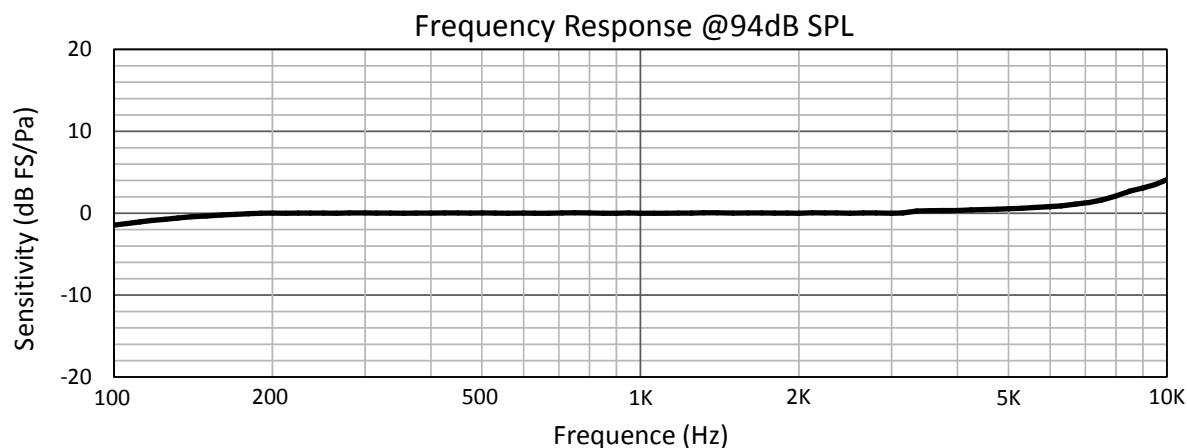


MICROPHONE STATE DIAGRAM

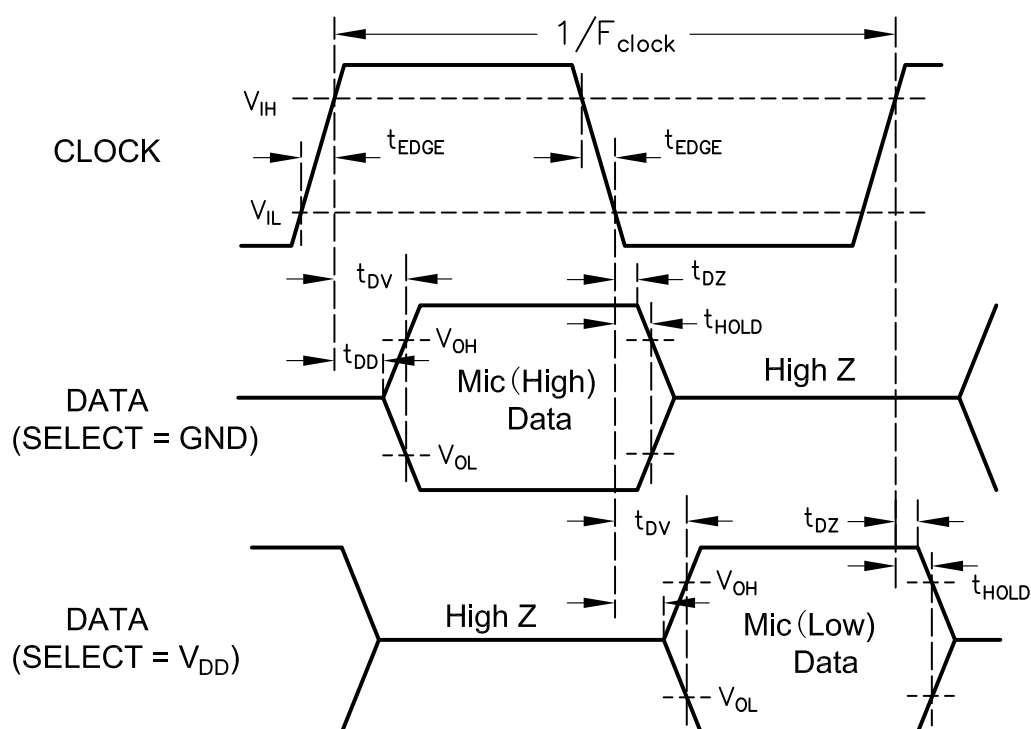




TYPICAL FREQUENCY RESPONSE



TIMING DIAGRAM

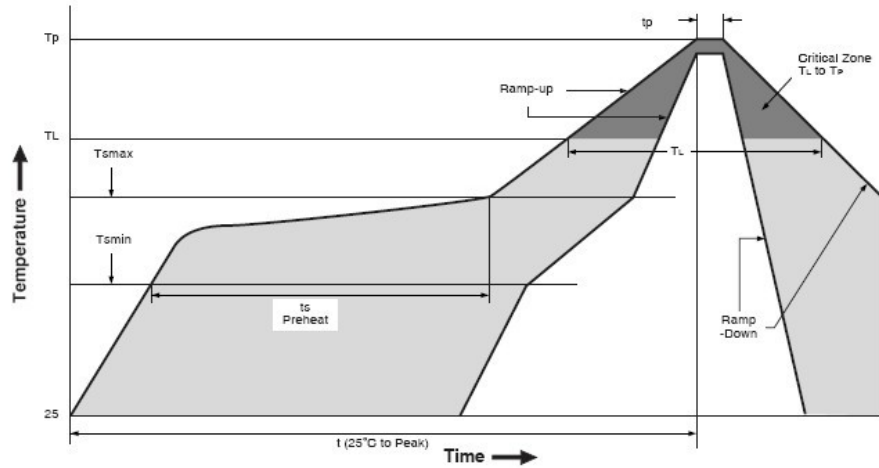


Parameter	Symbol	Min	Typ	Max
Clock Rise/Fall Time	t _{EDGE}	-	-	13ns
Delay Time to High Z	t _{DZ}	3ns	-	16ns
Delay Time to Data Line Driven	t _{DD}	18ns	28ns	40ns

※ t_{HOLD} and t_{DV} are related to load.



2. Recommend reflow profile:



Description	Parameter	Pb-free
Average ramp rate	T_L to T_P	3 °C/sec max
Preheat		
Minimum temperature	T_{SMIN}	150 °C
Maximum temperature	T_{SMAX}	200 °C
Time(T_{SMIN} to T_{SMAX})	t_s	60 sec to 120 sec
Ramp-up rate	T_{SMAX} to T_L	1.25 °C/sec max
Time maintained above liquidus temperature	t_L	60 sec to 150 sec
Liquidus temperature	T_L	217 °C
Peak temperature	T_P	260 °C max
Time within 5°C of actual peak temperature	t_p	20 sec to 40 sec
Ramp-down rate	T_L to T_P	6 °C/sec max
Time 25 °C ($t_{25\text{ °C}}$) to peak temperature	t	8 minutes max

MSM261D4030H1AP

PDM digital output MEMS microphone



苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



ADDITIONAL NOTES

- (A) MSL (moisture sensitivity level) Class 2a.
- (B) Maximum of 3 reflow cycles is recommended.
- (C) In order to minimize device damage:
 - Do not board wash or clean after the reflow process.
 - Do not brush board with or without solvents after the reflow process.
 - Do not directly expose to ultrasonic processing, welding, or cleaning.
 - Do not insert any object in port hole of device at any time.
 - Do not apply air pressure into the port hole.
 - Do not pull a vacuum over port hole of the microphone.

MATERIALS STATEMENT

Meets the requirements of the European RoHS and Halogen-Free.

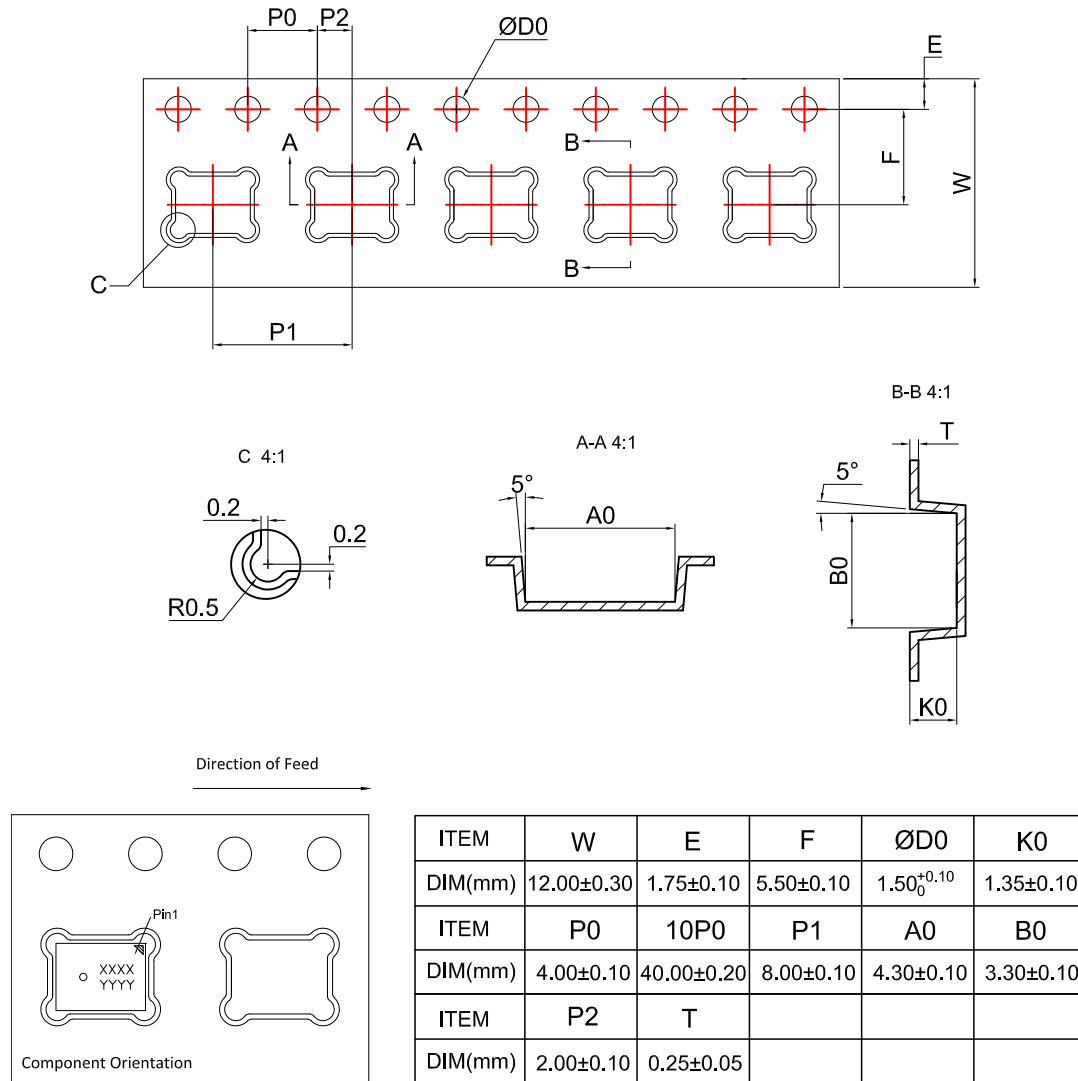
MSM261D4030H1AP

PDM digital output MEMS microphone

苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



PACKAGING & MARKING DETAIL:



Note:

- 1) Dimensions are in mm;
- 2) Don't put the vacuum suction nozzle alignment the port hole;
- 3) Tape & Reel Per EIA-481 standard;
- 4) Label applied to external package and direct to reel;
- 5) Static voltage <100V;

Model Number	Reel Diameter	Quantity Per Reel
MSM261D4030H1AP	13 inch	5700



RECOMMENDED INTERFACE CIRCUIT:

Figure 1. MSM261D4030H1AP electrical connections

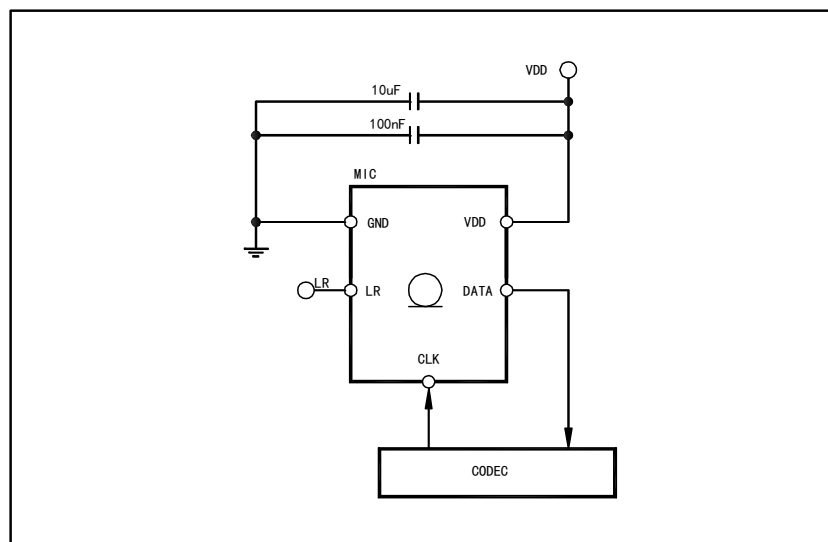
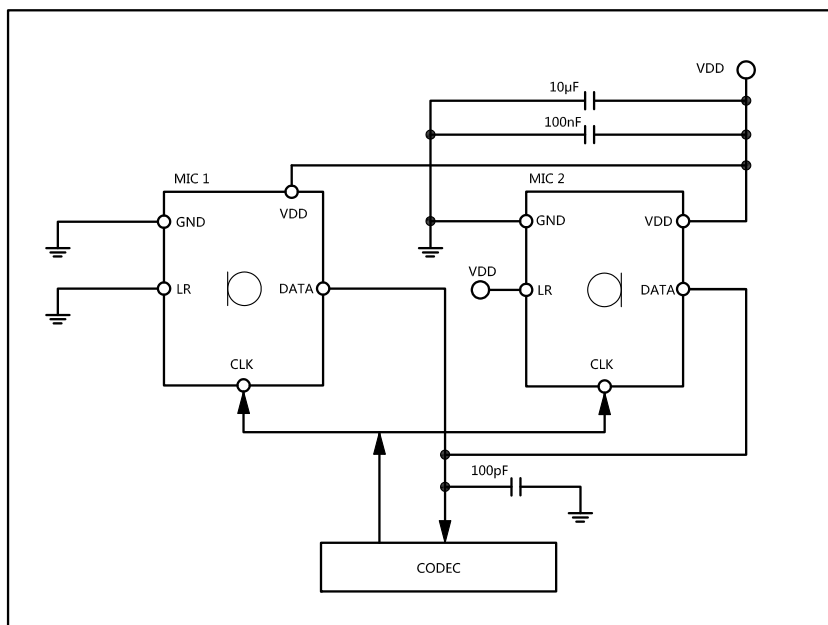


Figure 2. Electrical connections for stereo configurations



Power supply decoupling capacitors (100nF ceramic, 10uF ceramic) should be placed as near as possible to VDD of the device. (common design practice)



RELIABILITY SPECIFICATIONS

Test	Description
Thermal Shock	100 cycles air-to-air thermal shock from -40°C to +125°C with 15 minute soaks. (IEC 68-2-4)
High Temperature Storage	1,000 hours at +105°C environment (IEC 68-2-2 Test Ba)
Low Temperature Storage	1,000 hours at -40°C environment (IEC 68-2-2 Test Aa)
Reflow	5 reflow cycles with peak temperature of +260°C
ESD-HBM/LID-GND	3 discharges of ± 2 kV direct contact to I/O pins. (MIL 883E, Method 3015.7)& 3 discharges of ± 8 kV direct contact to lid while unit is grounded. (IEC 61000-4-2)
Vibration	4 cycles of 20 to 2,000 Hz sinusoidal sweep with 20 G peak acceleration lasting 12 minutes in X, Y and Z directions. (Mil-Std-883E, Method 2007.2 A)
Mechanical Shock	3 pulses of 3,000 G in the X, Y and Z direction (IEC 68-2-27, Test Ea)
High Temperature Bias	1,000 hours at +105°C under bias (IEC 68-2-2 Test Ba)
Low Temperature Bias	1,000 hours at -40°C under bias (IEC 68-2-2 Test Aa)
Temperature/Humidity Bias	1,000 hours at +85°C/85% R.H. under bias. (JESD22-A101A-B)
Drop Test	To be no interference in operation after dropped to 1.0cm steel plate 18 times from 1.5 meter height

NOTE: Sensitivity should vary within ± 3 dB from initial sensitivity. (The measurement to be done after 2 hours of conditioning at $20 \pm 2^\circ\text{C}$, R.H 60%~70%)

MSM261D4030H1AP
PDM digital output MEMS microphone



苏州敏芯微电子技术股份有限公司
MEMSensing Microsystems (Suzhou, China) Co., Ltd.



REVISION HISTORY:

Revision	Subjects (major changes since last revision)	Date
1.0	Initial Release	2016-10-31
1.1	Modified the Timing diagram	2017-1-16
1.2	Modified the Interface Circuit	2017-07-11
1.3	Update packaging detail	2017-10-24

公司销售、技术支持联系方式

(<http://www.memsensing.com>)

For English:

MEMSensing Microsystems(Suzhou,China)
Co. Ltd.

No. 99 Jinji Lake Avenue, Bldg. NW-09, Suite 501
Suzhou Industrial Park, China 215123

Phone: +86 512 62956055

Fax: +86 512 62956056

中文用户:

苏州敏芯微电子技术股份有限公司

苏州工业园区金鸡湖大道 99 号, NW-09 楼, 501 室
中国 215123

电话: +86 512 62956055

传真: +86 512 62956056

Disclaimer: specifications and characteristics are subject to change without notice. MEMSensing Microsystems Co. Ltd. assumes no liability to any customer, licensee or any third party for any damages or any kind of nature whatsoever related to using this technical data.